

HD74ALVC1G126

Bus Buffer Gate with 3-state Output

REJ03D0130-0300Z (Previous ADE-205-618B (Z)) Rev.3.00 Nov.12.2003

Description

The HD74ALVC1G126 has a bus buffer gate with 3-state output in a 5 pin package. Output is disabled when the associated output enable (OE) input is low. To ensure the high impedance state during power up or power down, OE should be connected to GND through a pull-down resistor; the minimum value of the resistor is determined by the current sourcing capability of the driver. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

Features

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Supply voltage range: 1.2 to 3.6 V

 Operating temperature range: -40 to +85°C
- All inputs V_{IH} (Max.) = 3.6 V (@ V_{CC} = 0 V to 3.6 V)

All outputs
$$V_0$$
 (Max.) = 3.6 V (@ V_{CC} = 0 V)

• Output current $\pm 2 \text{ mA } (@V_{CC} = 1.2 \text{ V})$

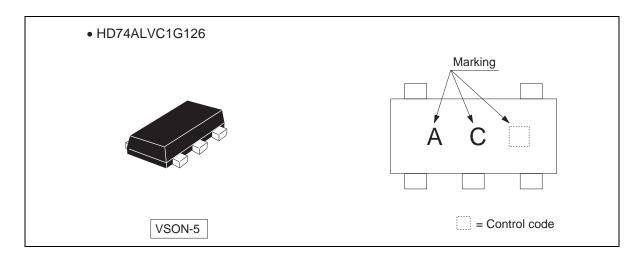
 ± 4 mA (@V_{CC} = 1.4 V to 1.6 V) ± 6 mA (@V_{CC} = 1.65 V to 1.95 V) ± 18 mA (@V_{CC} = 2.3 V to 2.7 V)

 $\pm 24 \text{ mA}$ (@ $V_{CC} = 3.0 \text{ V}$ to 3.6 V)

Ordering Information

			Package	Taping Abbreviation
Part Name	Package Type	Package Code	Abbreviation	(Quantity)
HD74ALVC1G126VSE	VSON-5 pin	TNP-5DV	VS	E (3,000 pcs/reel)

Outline and Article Indication



Function Table

Inputs

OE	A	Output Y
Н	Н	Н
Н	L	L
L	X	Z

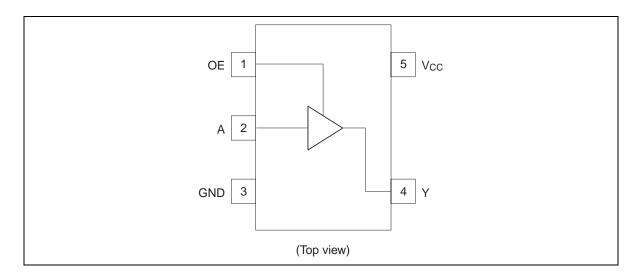
H: High level

L: Low level

X: Immaterial

Z: High impedance

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V _{CC}	-0.5 to 4.6	V	
Input voltage range *1	Vı	-0.5 to 4.6	V	
Output voltage range *1, 2	Vo	-0.5 to V _{CC} +0.5	V	Output : H or L or Z
		-0.5 to 4.6		V _{CC} : OFF
Input clamp current	I _{IK}	-50	mA	V _I < 0
Output clamp current	I _{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	lo	±50	mA	$V_O = 0$ to V_{CC}
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±100	mA	
Maximum power dissipation at Ta = 25°C (in still air) *3	P _T	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

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Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V _{CC}	1.2	3.6	V	
Input voltage range	VI	0	3.6	V	
Output voltage range	Vo	0	Vcc	V	
Output current	I _{OH}	_	-2	mA	V _{CC} = 1.2 V
		_	-4		V _{CC} = 1.4 V
		_	-6		V _{CC} = 1.65 V
		_	-18		V _{CC} = 2.3 V
		_	-24		V _{CC} = 3.0 V
	I _{OL}	_	2		V _{CC} = 1.2 V
		_	4		V _{CC} = 1.4 V
			6		V _{CC} = 1.65 V
			18		V _{CC} = 2.3 V
		_	24		V _{CC} = 3.0 V
Input transition rise or fall rate	Δt / Δν	0	20	ns / V	V _{CC} = 1.2 to 2.7 V
		0	10		V _{CC} = 3.3±0.3 V
Operating free-air temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}C)$

Item	Symbol	$V_{CC}(V)^*$	Min	Тур	Max	Unit	Test conditions
Input voltage	V _{IH}	1.2	V _{CC} ×0.75	_	_	V	
		1.4 to 1.6	V _{CC} ×0.7	_	_	_	
		1.65 to 1.95	V _{CC} ×0.7	_	_	_	
		2.3 to 2.7	1.7	_	_	_	
		3.0 to 3.6	2.0	_	_	_	
	V _{IL}	1.2	_	_	V _{CC} ×0.25	_	
		1.4 to 1.6	_	_	V _{CC} ×0.3	_	
		1.65 to 1.95	_	_	V _{CC} ×0.3	_	
		2.3 to 2.7	_	_	0.7	_	
		3.0 to 3.6	_	_	0.8	=	
Output voltage	V _{OH}	Min to Max	V _{CC} -0.2	_	_	V	$I_{OH} = -100 \mu A$
		1.2	0.9	_	_	=	$I_{OH} = -2 \text{ mA}$
		1.4	1.1	_	_	=	$I_{OH} = -4 \text{ mA}$
		1.65	1.2	_	_	=	$I_{OH} = -6 \text{ mA}$
		2.3	1.7	_	_	=	$I_{OH} = -18 \text{ mA}$
		3.0	2.2	_	_	=	$I_{OH} = -24 \text{ mA}$
	V _{OL}	Min to Max	_	_	0.2	=	$I_{OL} = 100 \mu\text{A}$
		1.2	_	_	0.3	_	I _{OL} = 2 mA
		1.4	_	_	0.3	=	I _{OL} = 4 mA
		1.65	_	_	0.3	=	I _{OL} = 6 mA
		2.3	_	_	0.55	_	I _{OL} = 18 mA
		3.0	_	_	0.55	=	I _{OL} = 24 mA
Input current	I _{IN}	3.6	_	_	±5	μΑ	V _{IN} = 3.6 V or GND
Off state output current	l _{OZ}	3.6	_	_	±5	μΑ	$V_O = V_{CC}$ or GND
Quiescent supply current	I _{CC}	3.6	_	_	10	μΑ	$V_{IN} = V_{CC}$ or GND, $I_O = 0$
Output leakage current	I _{OFF}	0	_	_	5	μΑ	V _{IN} or V _O = 0 to 3.6 V
Input capacitance	C _{IN}	3.3	_	4.0	_	pF	$V_{IN} = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

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Switching Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}C)$

 $V_{CC} = 1.2 \text{ V}$

Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	_	5.5	_	ns	$C_L = 15 pF$	Α	Υ
Enable time	t _{zH} t _{zL}	_	6.0	_	ns	C _L = 15 pF	OE	Y
Disable time	t _{HZ} t _{LZ}	_	4.5	_	ns	C _L = 15 pF	OE	Y

 $V_{CC} = 1.5 \pm 0.1 \text{ V}$

Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	2.0	_	7.0	ns	$C_L = 15 pF$	Α	Υ
Enable time	t _{ZH} t _{ZL}	2.0	_	7.0	ns	C _L = 15 pF	OE	Υ
Disable time	t _{HZ} t _{LZ}	2.0	_	7.0	ns	C _L = 15 pF	OE	Υ

 $V_{CC} = 1.8 \pm 0.15 \text{ V}$

Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	1.5	_	5.0	ns	$C_L = 30 pF$	Α	Υ
Enable time	t _{ZH} t _{ZL}	1.5	_	5.0	ns	C _L = 30 pF	OE	Y
Disable time	t _{HZ} t _{LZ}	1.5	_	5.0	ns	C _L = 30 pF	OE	Y

Switching Characteristics (cont)

 $V_{CC} = 2.5 \pm 0.2 \text{ V}$

Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	1.0	_	4.0	ns	$C_L = 30 pF$	Α	Υ
Enable time	t _{ZH} t _{ZL}	1.0	_	4.0	ns	$C_L = 30 pF$	OE	Υ
Disable time	t _{HZ} t _{LZ}	1.0	_	4.0	ns	$C_L = 30 pF$	OE	Υ

 $V_{CC} = 3.3 \pm 0.3 \text{ V}$

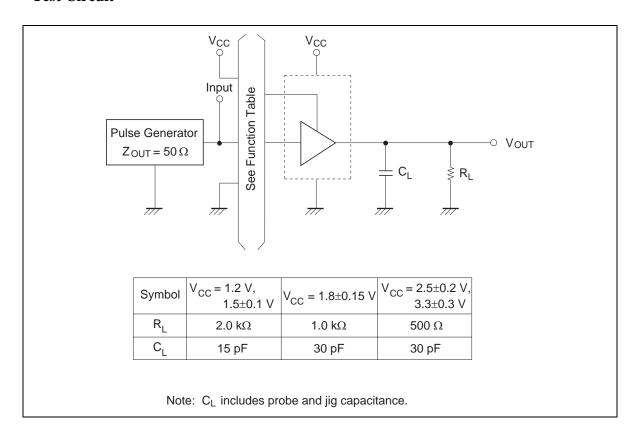
Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	1.0	_	3.0	ns	$C_L = 30 pF$	Α	Υ
Enable time	t _{ZH} t _{ZL}	1.0	_	3.0	ns	C _L = 30 pF	OE	Y
Disable time	t _{HZ} t _{LZ}	1.0	_	3.0	ns	$C_L = 30 pF$	OE	Y

Operating Characteristics

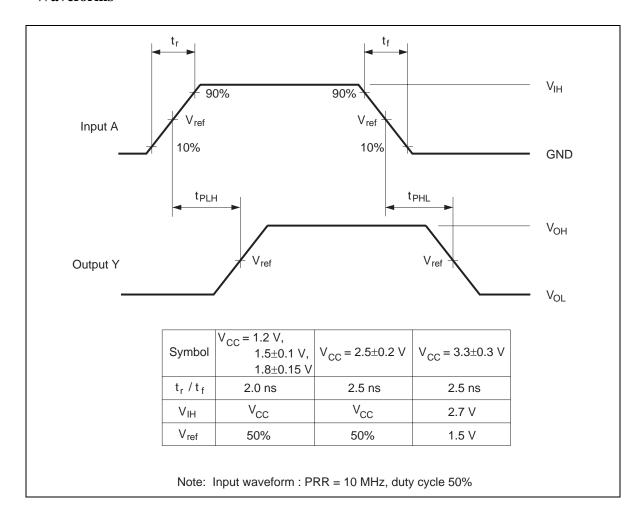
 $(Ta = 25^{\circ}C)$

Item	Symbol	V _{CC} (V)	Min	Тур	Max	Unit	Test conditions
Power dissipation capacitance	C _{PD}	1.5	_	9.5	_	pF	f = 10 MHz
		1.8	_	9.5	_	_	
		2.5	_	10.0	_		
		3.3		11.0	_	_	

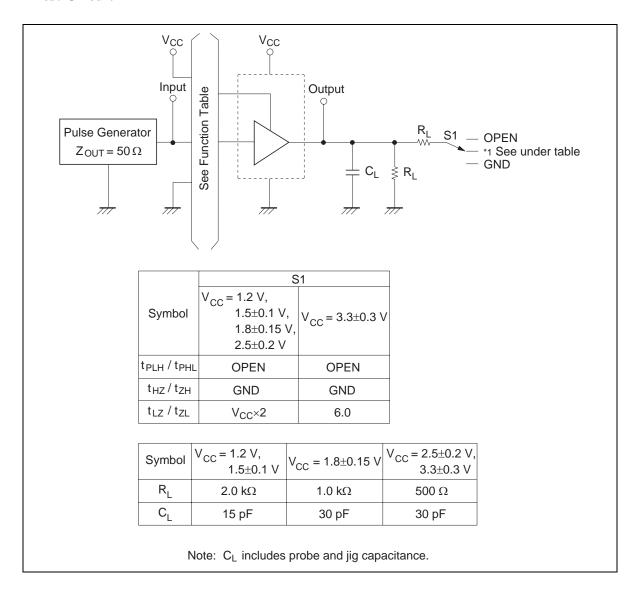
Test Circuit



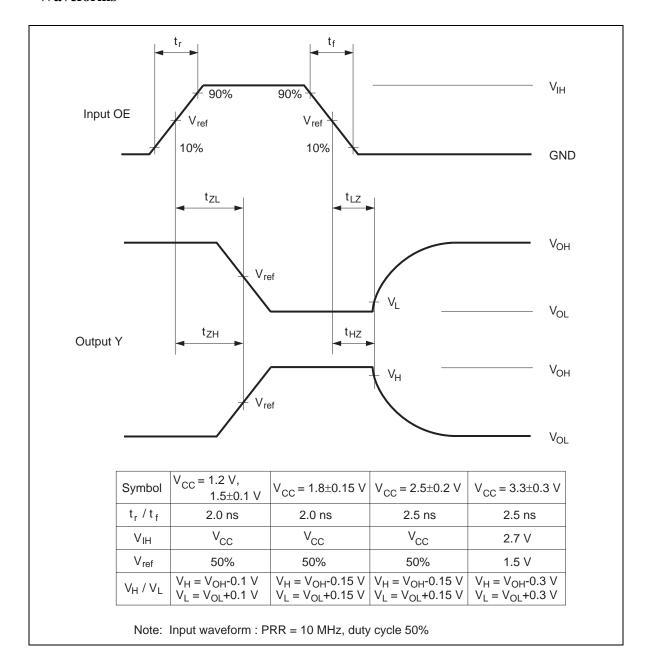
Waveforms



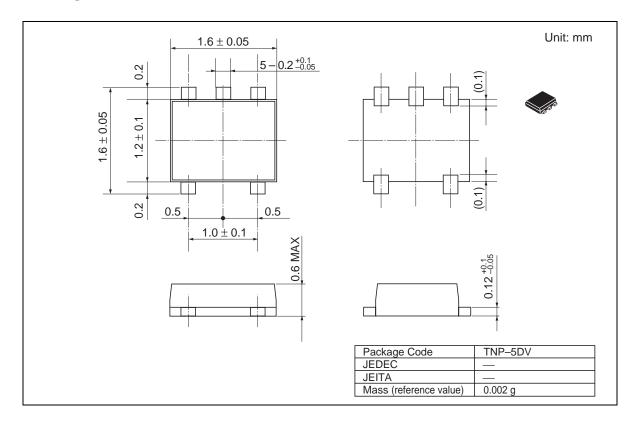
Test Circuit



Waveforms



Package Dimensions



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